

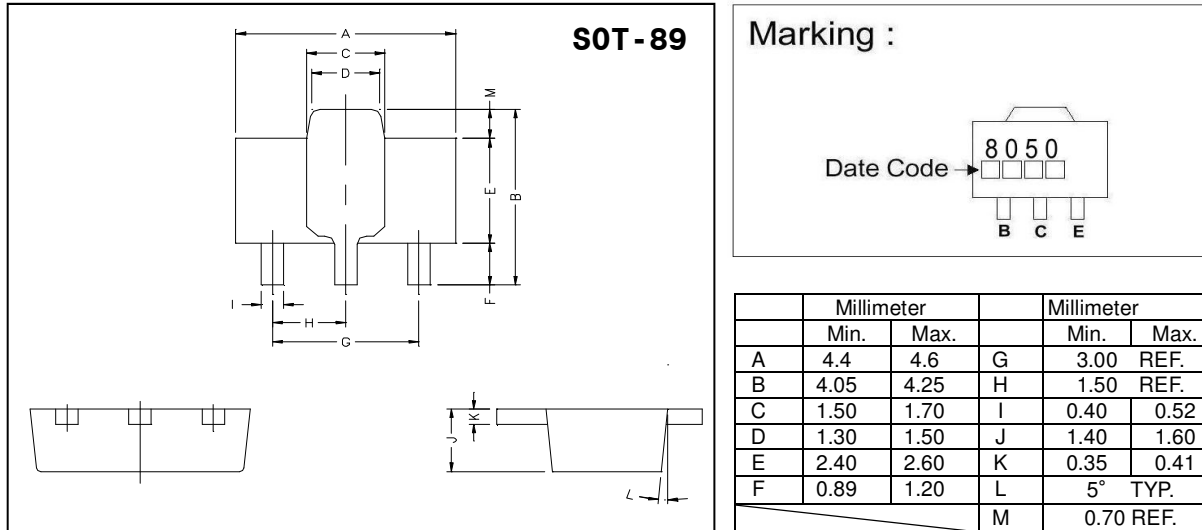
GM8050

NPN EPITAXIAL TRANSISTOR

Description

The GM8050 is designed for general purpose amplifier applications.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CBO}	40	V
Collector to Emitter Voltage	V _{CEO}	25	V
Emitter to Base Voltage	V _{EBO}	6	V
Collector Current	I _C	1.5	A
IB Base Current	I _B	0.5	A
Total Power Dissipation	P _D	1	W

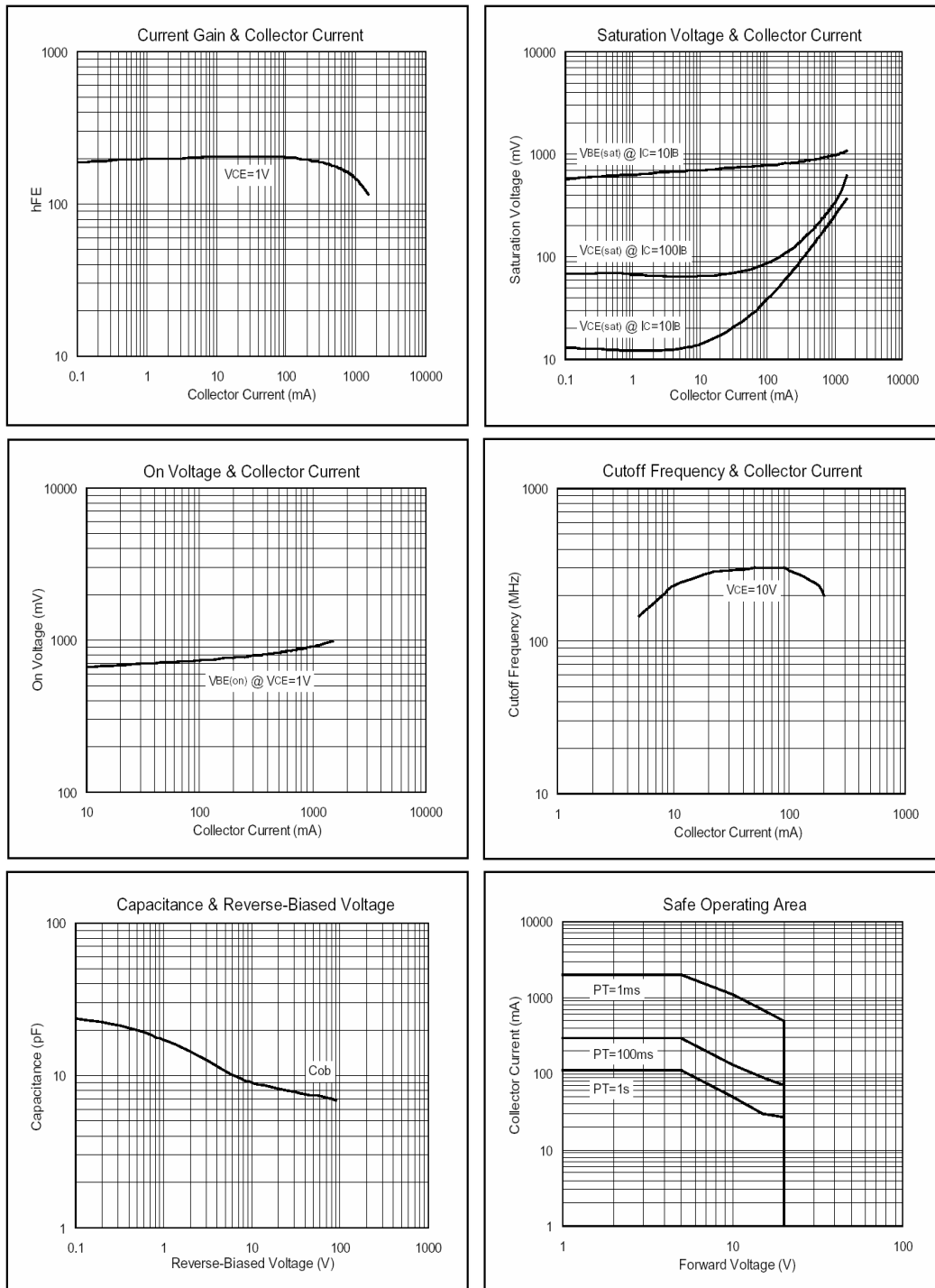
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
B _V C _{BO}	40	-	-	V	I _C =100uA
B _V C _{EO}	25	-	-	V	I _C =2mA
B _V E _{BO}	6	-	-	V	I _E =100uA
I _C B _O	-	-	100	nA	V _{CB} =35V
I _E B _O	-	-	100	nA	V _{EB} =6V
V _{CE} (sat)	-	-	0.5	V	I _C =0.8A, I _B =80mA
V _{BE} (sat)	-	-	1.2	V	I _C =0.8A, I _B =80mA
V _{BE} (on)	-	-	1	V	V _{CE} =1V, I _C =10mA
H _{fe} 1	45	-	-		V _{CE} =1V, I _C =5mA
H _{fe} 2	120	-	500		V _{CE} =1V, I _C =100mA
H _{fe} 3	40	-	-		V _{CE} =1V, I _C =800mA
f _T	100	-	-	MHz	V _{CE} =10V, I _C =50mA

Classification Of hFE

Rank	C	D	E
hFE	120-200	160 - 300	250 - 500

Characteristics Curve



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